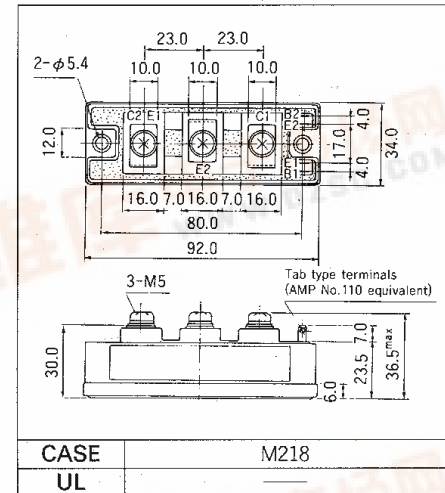


FUJI
ELECTRIC**2MBI 50L-120****2-Pack IGBT**
1200 V
50 A**IGBT MODULE (L series)****■ Features**

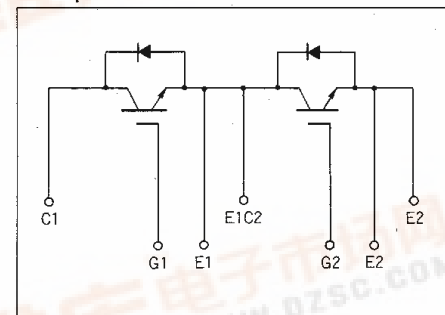
- High Speed Switching
- Low Saturation Voltage
- Voltage Drive

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial Machines, such as Welding Machines

■ Outline Drawings**■ Maximum Ratings and Characteristics****● Absolute Maximum Ratings**

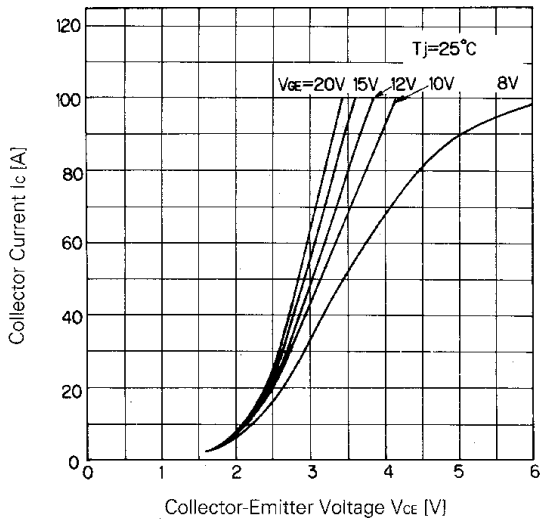
Items		Symbols	Ratings	Units
Collector-Emitter Voltage		V_{CES}	1200	V
Gate-Emitter Voltage		V_{GES}	± 20	V
Collector Current	Continuous	I_C	50	A
	1ms	$I_C \text{ pulse}$	100	
	Continuous	$-I_C$	50	
	1ms	$-I_C \text{ pulse}$	100	
Max. Power Dissipation		P_C	400	W
Operating Temperature		T_j	+150	$^{\circ}\text{C}$
Storage Temperature		T_{stg}	-40 to +125	$^{\circ}\text{C}$
Net. Weight			185	g
Isolation Voltage	AC, 1min.	V_{isol}	2500	V
Screw Torque		Mounting *1	35	kg $\cdot$ cm
		Terminals *2	35	

■ Equilavelent Circuit Schematic*1 Recommendable Value 25 to 35kg $\cdot$ cm (M5)*2 Recommendable Value 25 to 35kg $\cdot$ cm (M5)**● Electrical Characteristics ($T_c=25^{\circ}\text{C}$)**

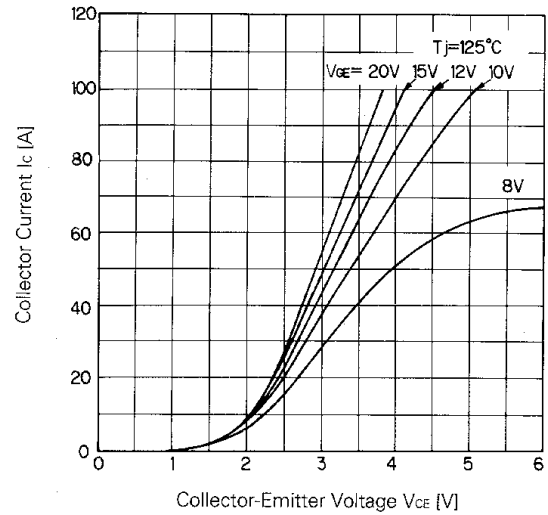
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE}=0V$ $V_{CE}=1200V$ $T_c=25^{\circ}\text{C}$			1.0	mA
		$V_{GE}=0V$ $V_{CE}=1200V$ $T_c=125^{\circ}\text{C}$			—	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0V$ $V_{GE}=\pm 20V$			100	nA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}=20V$ $I_C=50mA$	3.0		6.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V$ $I_C=50A$		2.7	3.5	V
Input Capacitance	C_{ies}	$V_{GE}=0V$		9000		pF
Output Capacitance	C_{oes}	$V_{CE}=10V$		—		
Reverse Transfer Capacitance	C_{res}	$f=1MHz$		—		
Turn-on Time	t_{on}	$V_{CC}=600V$		0.5	0.8	μs
	t_r	$I_C=50A$		0.3	0.6	
Turn-off Time	t_{off}	$V_{GE}=\pm 15V$		0.8	1.5	
	t_f	$R_G=25\Omega$		0.3	0.5	
Diode Forward On-Voltage	V_F	$I_F=50A$ $V_{GE}=0V$			2.5	V
Reverse Recovery Time	t_{rr}	$I_F=50A$ $-di/dt=150A/\mu\text{s}$ $V_{GE}=-10V$		200	350	ns

● Thermal Characteristics

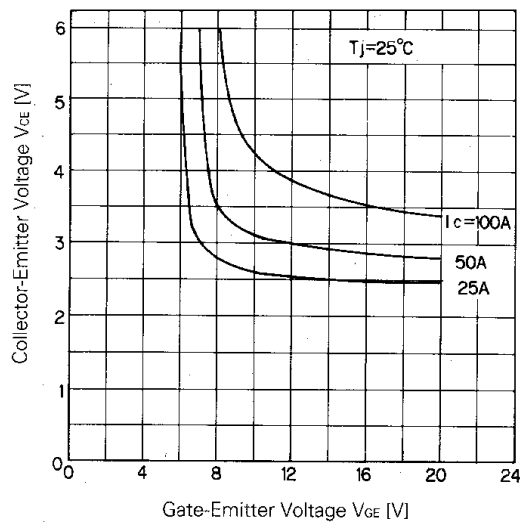
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	$R_{th(j-c)}$	IGBT			0.312	$^{\circ}\text{C/W}$
	$R_{th(j-e)}$	Diode			0.60	
	$R_{th(c-f)}$	With Thermal compound		0.05		



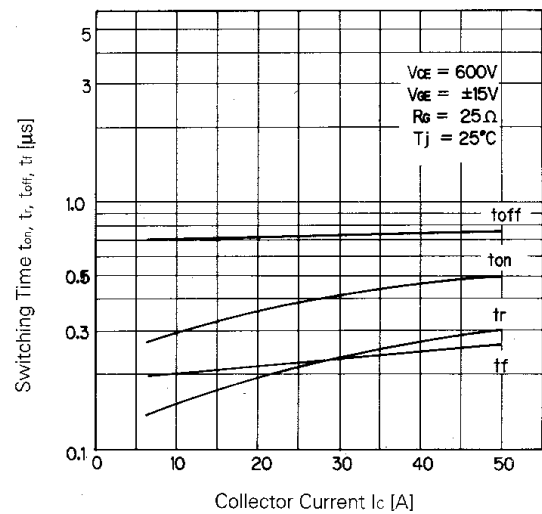
Collector Current vs. Collector-Emitter Voltage



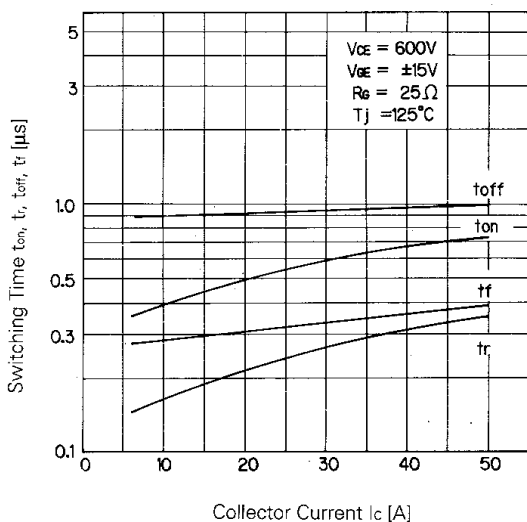
Collector Current vs. Collector-Emitter Voltage



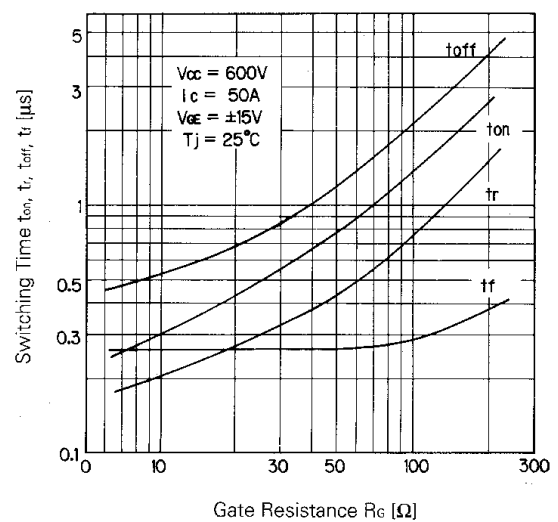
Collector-Emitter Voltage vs. Gate-Emitter Voltage



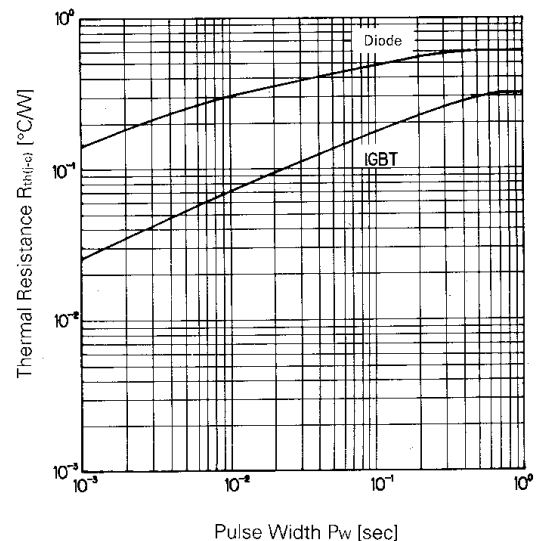
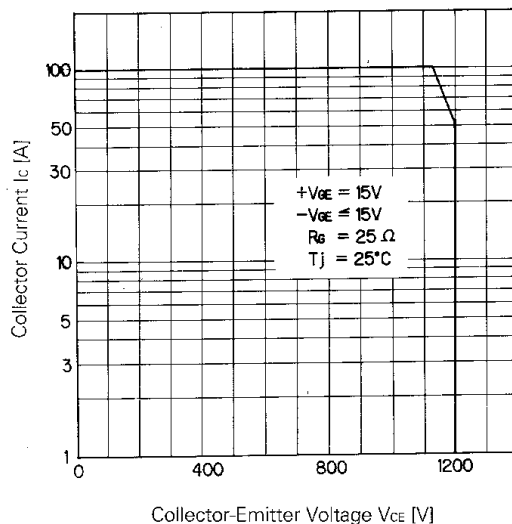
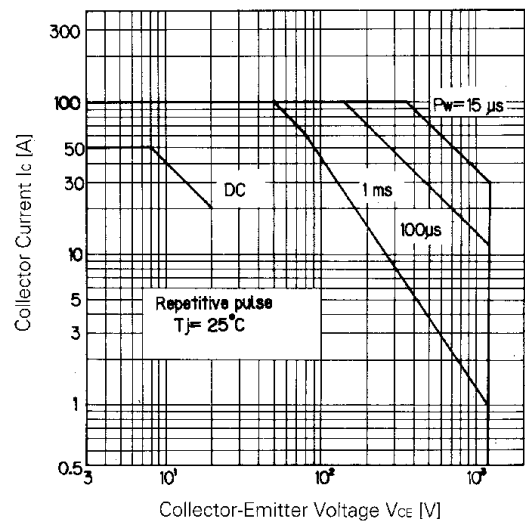
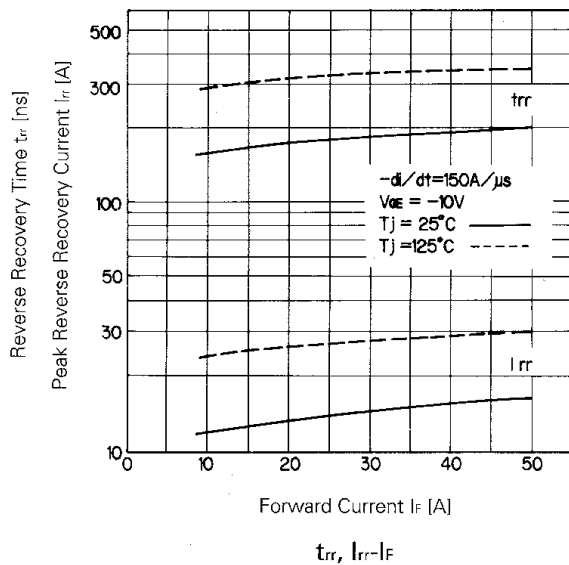
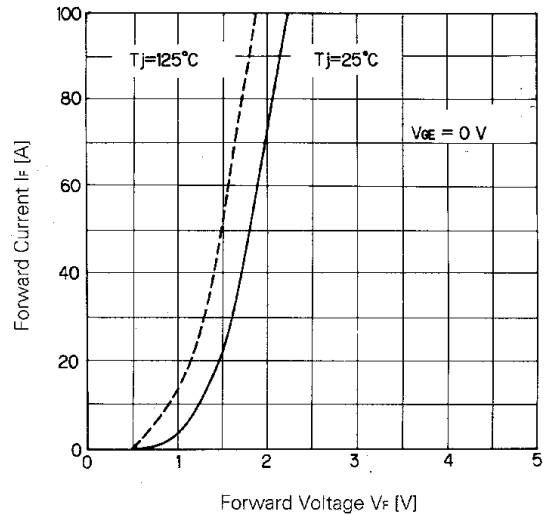
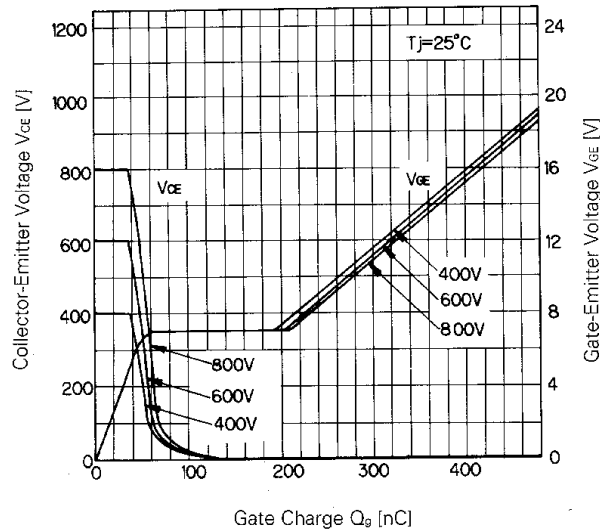
Switching Time



Switching Time



Switching Time-Gate Resistance



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